Amendments to the Claims

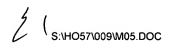
- 1. (Previously presented) A sputtering target made by a process including casting having a target surface with the following characteristics:
 - a) substantially homogenous composition at any location;
 - b) substantial absence of pores, voids, inclusions and other casting defects;
 - c) an absence of detectable precipitates;
 - d) an average grain size of less than 1µm; and
 - e) substantially uniform structure and texture at any location.
- 2. (Previously presented) A sputtering target according to claim 1 comprising one or more of Al, Ti, Cu, Ta, Ni, Mo, Au, Ag, and Pt.
- 3. (Original) A sputtering target according to claim 1 comprising Al and about 0.5 wt.% Cu.

Claims 4-44 (Cancelled).

- 45. (Previously presented) The sputtering target of claim 1 comprising an alloy which includes at least one of Al, Ti, Cu, Ta, Ni, Mo, Au, Ag and Pt.
 - 46. (Previously presented) The sputtering target of claim 1 comprising Al.
 - 47. (Previously presented) The sputtering target of claim 1 comprising Ti.

- 48. (Previously presented) The sputtering target of claim 1 comprising Cu.
- 49. (Previously presented) The sputtering target of claim 1 comprising Ta.
- 50. (Previously presented) The sputtering target of claim 1 comprising Ni.
- 51. (Previously presented) The sputtering target of claim 1 comprising Mo.
- 52. (Previously presented) The sputtering target of claim 1 comprising Au.
- 53. (Previously presented) The sputtering target of claim 1 comprising Ag.
- 54. (Previously presented) The sputtering target of claim 1 comprising Pt.
- 55. (Currently amended) A sputtering target formed from a cast material and comprising:
- a yield strength of greater than 50 mega pascal Pascal (MP), and an ultimate tensile strength of greater than 125 MP;
- a substantial absence of pores, voids and inclusions; and
 an average grain size of less than about 1 µm, the target having an annealed
 upper surface portion and a remaining portion that is un-annealed.

- 56. (Previously presented) The sputtering target of claim 55 comprising one or more of Al, Ti, Cu, Ta, Ni, Mo, Au, Ag, and Pt.
- 57. (Previously presented) The sputtering target of claim 55 comprising an alloy which includes at least one of Al, Ti, Cu, Ta, Ni, Mo, Au, Ag and Pt.
- 58. (Previously presented) The sputtering target of claim 55 further comprising a substantial absence of precipitates.
- 59. (Previously presented) The sputtering target of claim 55 further comprising a substantially uniform structure and texture at any location.
- 60. (Previously presented) The sputtering target of claim 55 further comprising a substantially homogeneous composition at any location.
- 61. (Currently amended) A copper sputtering target comprising copper, formed by a process including casting, and having a target surface with the following characteristics:
 - a) substantially homogenous composition at any location;
 - b) substantial absence of pores, voids, inclusions and other casting defects;
 - c) an absence of detectable precipitates;
 - d) an average grain size less than about 1µm; and
 - e) substantially uniform structure and texture at any location.



- 62. (Previously presented) The sputtering target of claim 1 further comprising one or more of Al, Au, and Ag.
 - 63. (Previously presented) The sputtering target of claim 62 comprising Al.
 - 64. (Previously presented) The sputtering target of claim 62 comprising Au.
 - 65. (Previously presented) The sputtering target of claim 62 comprising Ag.
- 66. (Previously presented) A sputtering target formed from a cast copper material and comprising:
- a yield strength of greater than 50 mega Pascal (MP), and an ultimate tensile strength of greater than 125 MP;
 - a substantial absence of pores, voids and inclusions; and an average grain size of less than about 1 μm .
- 67. (Previously presented) The sputtering target of claim 66 wherein the copper material comprises pure copper.
- 68. (Previously presented) The sputtering target of claim 66 comprising one or more of AI, Au, and Ag.



- 69. (Previously presented) The sputtering target of claim 66 wherein the copper material comprises a copper alloy having one or more of the elements selected from the group consisting of Al, Au, and Ag.
- 70. (Previously presented) The sputtering target of claim 66 further comprising a substantial absence of precipitates.
- 71. (Previously presented) The sputtering target of claim 66 further comprising a substantially uniform structure and texture at any location.
- 72. (Previously presented) The sputtering target of claim 66 further comprising a substantially homogeneous composition at any location.
- 73. (Previously presented) The sputtering target of claim 55 wherein both the yield strength and the ultimate tensile strength are greater than 125 MP.
- 74. (Previously presented) The sputtering target of claim 55 wherein both the yield strength and the ultimate tensile strength are greater than 150 MP.

